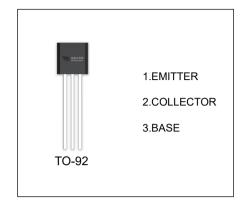


2SA836 TRANSISTOR (PNP)

FEATURES

- High DC Current Gain
- Low Frequency Amplifier



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA836	TO-92	Bulk	1000pcs/Bag
2SA836-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-55	V
V _{CEO}	Collector-EmitterVoltage	-55	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current	-0.1	Α
Pc	Collector Power Dissipation	200	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	625	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



$T_a \text{=} 25\,^\circ\!\!\subset\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	$I_C = -0.01 \text{mA}, I_E = 0$	-55			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA,I _B =0	-55			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.01mA,I _C =0	-5			٧
Collector cut-off current	I _{CBO}	V _{CB} =-18V,I _E =0			-0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =-2V,I _C =0			-0.05	μΑ
DC current gain	h _{FE}	V _{CE} =-12V, I _C =-2mA	160		500	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10mA,I _B =-1mA			-0.5	V
Base-emitter voltage	V_{BE}	V _{CE} =-12V, I _C =-2mA			-0.75	V
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _E =0, f=1MHz			4	pF
Transition frequency	f _T	Vc=-12V,lc=-2mA	150			MHz

CLASSIFICATION OF h_{FE}

RANK	С	D
RANGE	160-320	250-500



